



Features

- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive
- Avalanche Ruggedness
- Resistant to Latch-Up
- Halogen Free, RoHS Compliant

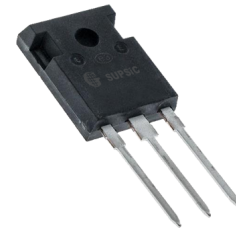
V_{DS}	1200 V
$I_D @ 25^\circ\text{C}$	90 A
$R_{DS(on)}$	25 m Ω

Benefits

- Higher System Efficiency
- Reduced Cooling Requirements
- Increased Power Density
- Increased System Switching Frequency

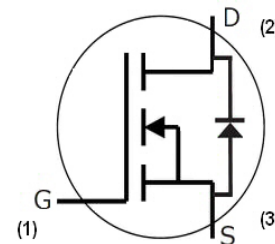
Applications

- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC/DC converters
- Battery Chargers
- Motor Drive
- Pulsed Power Applications



TO-247-3

Package



Part Number	Package	Marking
GC2M0025120D	TO-247-3	GC2M0025120

Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DSmax}	Drain - Source Voltage	1200	V	$V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$	
V_{GSmax}	Gate - Source Voltage	-10/+25	V	Absolute maximum values	
V_{GSop}	Gate - Source Voltage	-5/+20	V	Recommended operational values	
I_D	Continuous Drain Current	90	A	$V_{GS} = 20\text{ V}, T_C = 25^\circ\text{C}$	Fig. 19 Note 1
		60		$V_{GS} = 20\text{ V}, T_C = 100^\circ\text{C}$	
$I_{D(pulse)}$	Pulsed Drain Current	250	A	Pulse width t_p limited by T_{jmax}	Fig. 22
P_D	Power Dissipation	378	W	$T_c = 25^\circ\text{C}, T_J = 150^\circ\text{C}$	Fig. 20
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$		
T_L	Solder Temperature	260	$^\circ\text{C}$	1.6mm (0.063") from case for 10s	
M_d	Mounting Torque	1	Nm lbf-in	M3 or 6-32 screw	
		8.8			

Note (1): Die limits are 90A (25°C) and 60A (100°C)

Electrical Characteristics ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	1200			V	$V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$	
$V_{GS(th)}$	Gate Threshold Voltage	2.0	2.6	4	V	$V_{DS} = V_{GS}, I_D = 15\text{mA}$	Fig. 11
			2.3		V	$V_{DS} = V_{GS}, I_D = 15\text{mA}, T_J = 150^\circ\text{C}$	
I_{DSS}	Zero Gate Voltage Drain Current		2	100	μA	$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$	
I_{GSS}	Gate-Source Leakage Current			250	nA	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	
$R_{DS(on)}$	Drain-Source On-State Resistance		25	34	m Ω	$V_{GS} = 20\text{ V}, I_D = 50\text{ A}$	Fig. 4,5,6
			41			$V_{GS} = 20\text{ V}, I_D = 50\text{ A}, T_J = 150^\circ\text{C}$	
g_{fs}	Transconductance		24.6		S	$V_{DS} = 20\text{ V}, I_{DS} = 50\text{ A}$	Fig. 7
			24			$V_{DS} = 20\text{ V}, I_{DS} = 50\text{ A}, T_J = 150^\circ\text{C}$	
C_{iss}	Input Capacitance		3140		pF	$V_{GS} = 0\text{ V}$ $V_{DS} = 1000\text{ V}$ $f = 1\text{ MHz}$	Fig. 17,18
C_{oss}	Output Capacitance		224				
C_{rss}	Reverse Transfer Capacitance		9				
E_{oss}	C_{oss} Stored Energy		128		μJ	$V_{AC} = 25\text{ mV}$	Fig 16
E_{ON}	Turn-On Switching Energy (Body Diode)		2.18		mJ	$V_{DS} = 800\text{ V}, V_{GS} = -5/20\text{ V},$ $I_D = 50\text{A}, R_{G(ext)} = 2.5\Omega, L = 99\ \mu\text{H}$ FWD = Internal Body Diode of MOSFET	Fig. 25
E_{OFF}	Turn Off Switching Energy (Body Diode)		0.68				
E_{ON}	Turn-On Switching Energy (External SiC Diode)		1.14		mJ	$V_{DS} = 800\text{ V}, V_{GS} = -5/20\text{ V},$ $I_D = 50\text{A}, R_{G(ext)} = 2.5\Omega, L = 99\ \mu\text{H}$ FWD = External SiC Diode	Fig. 25
E_{OFF}	Turn Off Switching Energy (External SiC Diode)		0.8				
$t_{d(on)}$	Turn-On Delay Time		15		ns	$V_{DD} = 800\text{ V}, V_{GS} = -5/20\text{ V}$ $I_D = 50\text{ A},$ $R_{G(ext)} = 2.5\ \Omega,$ Inductive Load Timing relative to V_{DS} Per IEC60747-8-4 pg 83	Fig. 27
t_r	Rise Time		58				
$t_{d(off)}$	Turn-Off Delay Time		33				
t_f	Fall Time		17				
$R_{G(int)}$	Internal Gate Resistance		1.0		Ω	$f = 1\text{ MHz}, V_{AC} = 25\text{ mV}, \text{ESR of } C_{iss}$	
Q_{gs}	Gate to Source Charge		46		nC	$V_{DS} = 800\text{ V}, V_{GS} = -5/20\text{ V}$ $I_D = 50\text{ A}$ Per IEC60747-8-4 pg 21	Fig. 12
Q_{gd}	Gate to Drain Charge		71.5				
Q_g	Total Gate Charge		194				

Reverse Diode Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V _{SD}	Diode Forward Voltage	4.1		V	V _{GS} = - 5 V, I _{SD} = 25 A	Fig. 8, 9, 10
		3.5		V	V _{GS} = - 5 V, I _{SD} = 25 A, T _J = 150 °C	
I _S	Continuous Diode Forward Current		90	A	V _{GS} = - 5 V, T _C = 25 °C	Note 2
I _{S,pulse}	Diode Pulse Current		250	A	V _{GS} = - 5 V, Pulse width t _p limited by T _{Jmax}	
t _{rr}	Reverse Recovery Time	33		ns	V _{GS} = - 5 V, I _{SD} = 50 A, T _J = 25 °C VR = 800 V dif/dt = 2180 A/μs	Note 2
Q _{rr}	Reverse Recovery Charge	487		nC		
I _{rrm}	Peak Reverse Recovery Current	24		A		
t _{rr}	Reverse Recovery Time	67		ns	V _{GS} = - 5 V, I _{SD} = 50 A, T _J = 25 °C VR = 800 V dif/dt = 1320 A/μs	Note 2
Q _{rr}	Reverse Recovery Charge	386		nC		
I _{rrm}	Peak Reverse Recovery Current	15		A		

Note (2): When using SiC Body Diode the maximum recommended V_{GS} = -5V

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
R _{θJC}	Thermal Resistance from Junction to Case	0.24	0.33	°C/W		Fig. 21
R _{θJA}	Thermal Resistance from Junction to Ambient		40			

Typical Performance

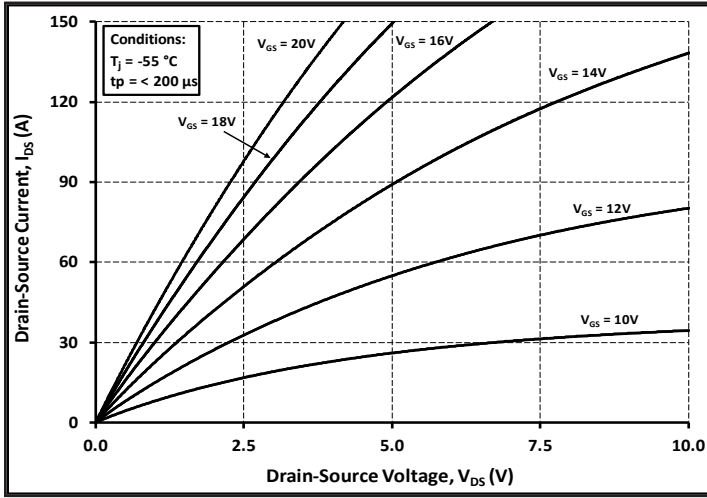


Figure 1. Output Characteristics $T_J = -55\text{ }^\circ\text{C}$

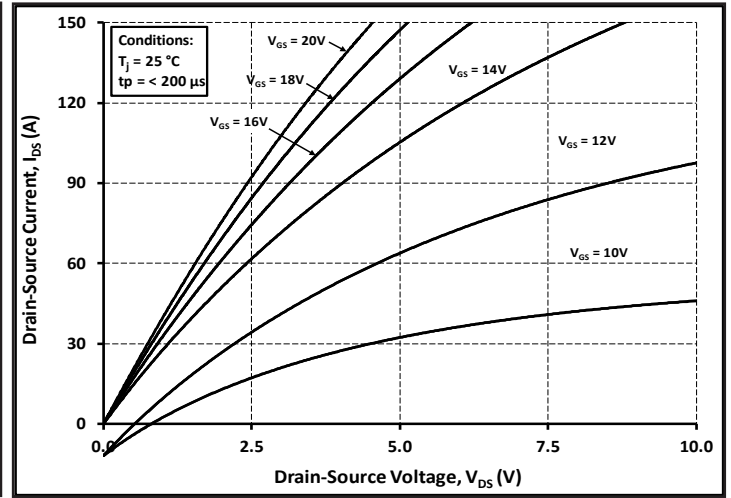


Figure 2. Output Characteristics $T_J = 25\text{ }^\circ\text{C}$

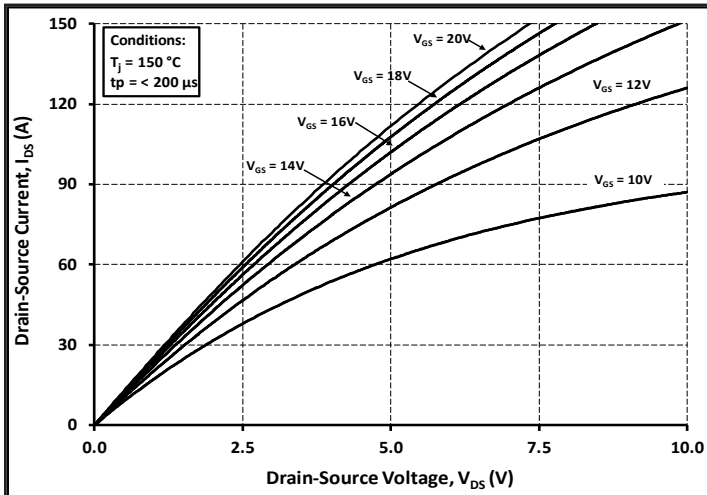


Figure 3. Output Characteristics $T_J = 150\text{ }^\circ\text{C}$

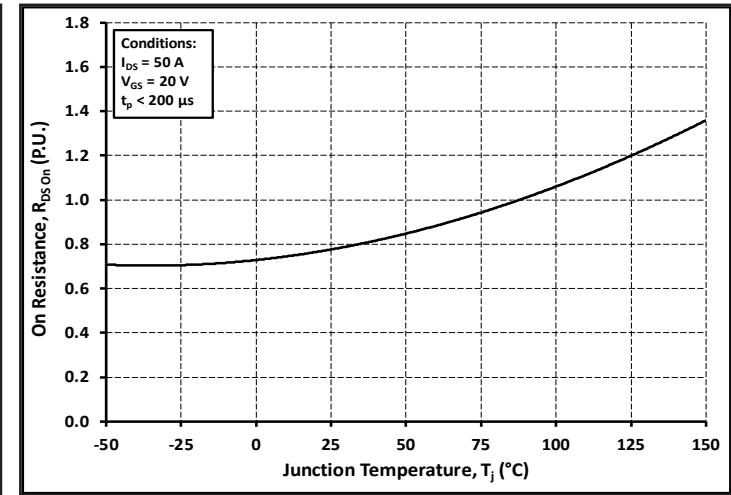


Figure 4. Normalized On-Resistance vs. Temperature

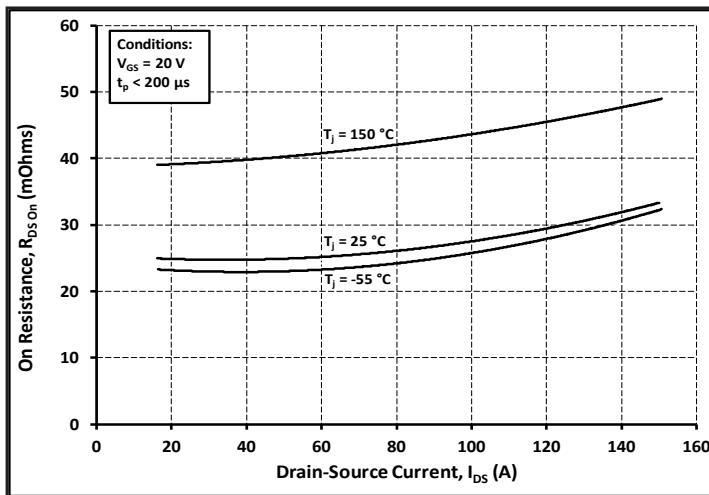


Figure 5. On-Resistance vs. Drain Current For Various Temperatures

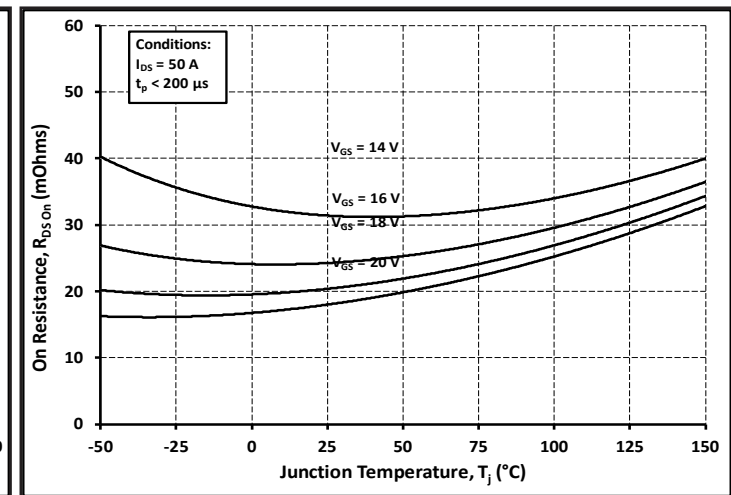


Figure 6. On-Resistance vs. Temperature For Various Gate Voltage

Typical Performance

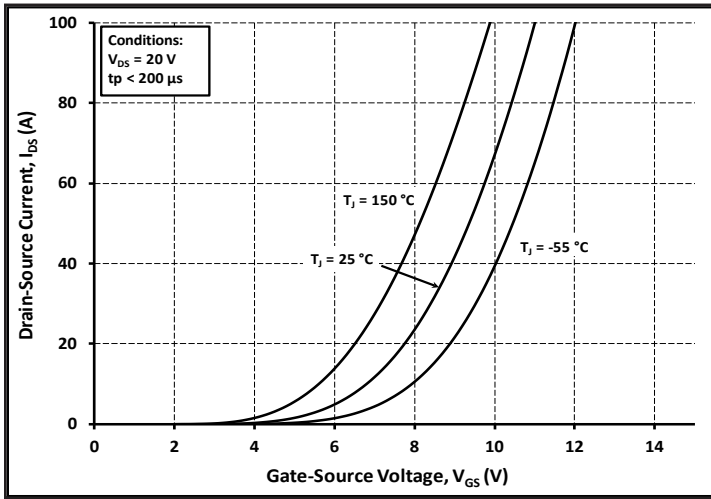


Figure 7. Transfer Characteristic For Various Junction Temperatures

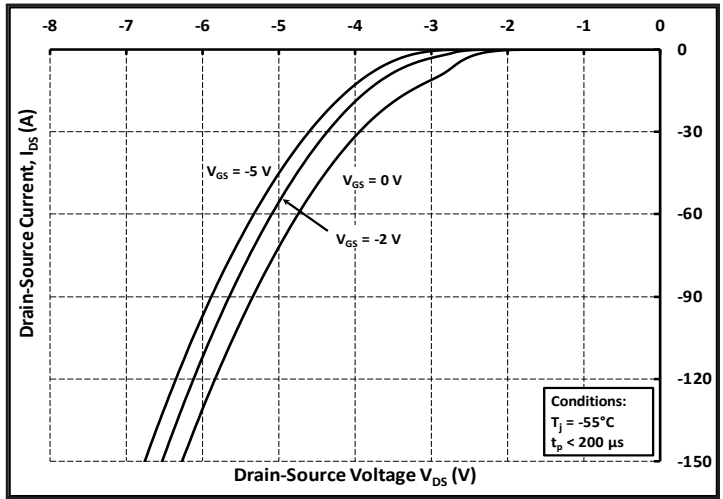


Figure 8. Body Diode Characteristic at -55 °C

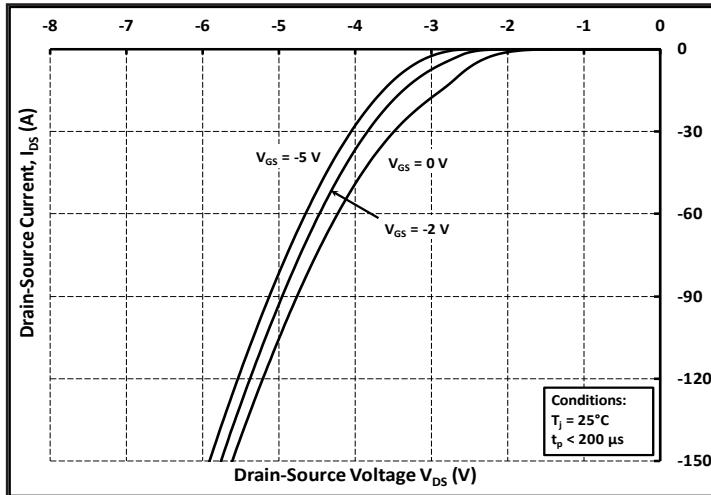


Figure 9. Body Diode Characteristic at 25 °C

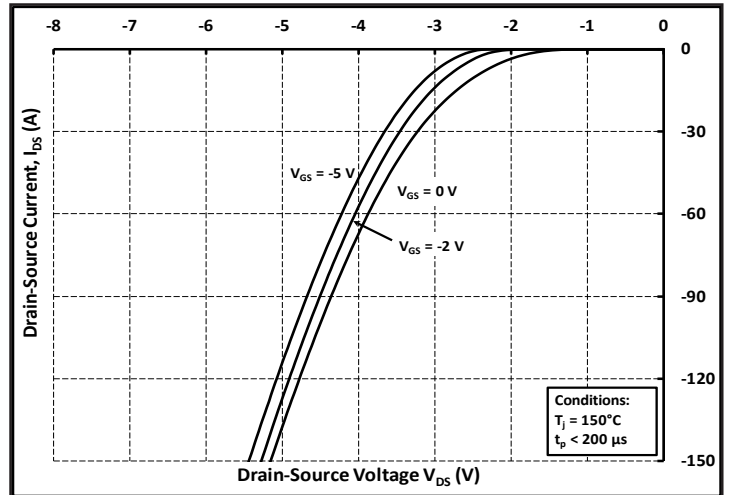


Figure 10. Body Diode Characteristic at 150 °C

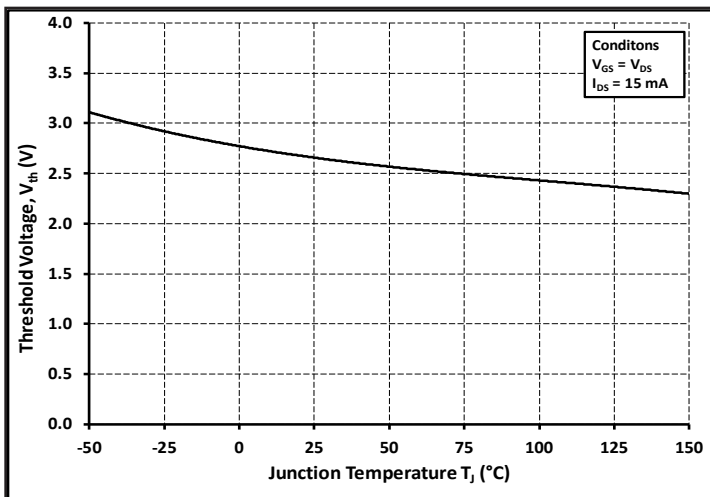


Figure 11. Threshold Voltage vs. Temperature

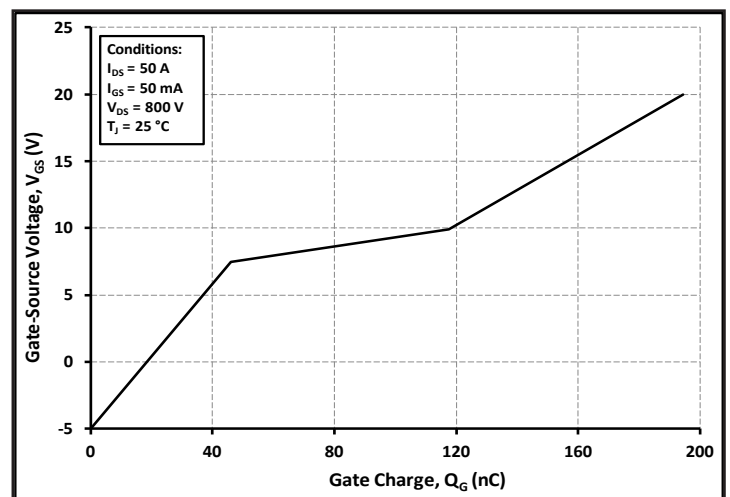


Figure 12. Gate Charge Characteristic

Typical Performance

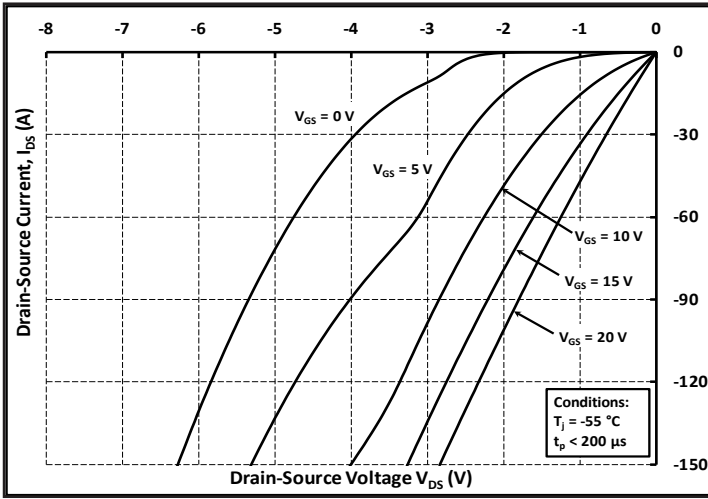


Figure 13. 3rd Quadrant Characteristic at -55 °C

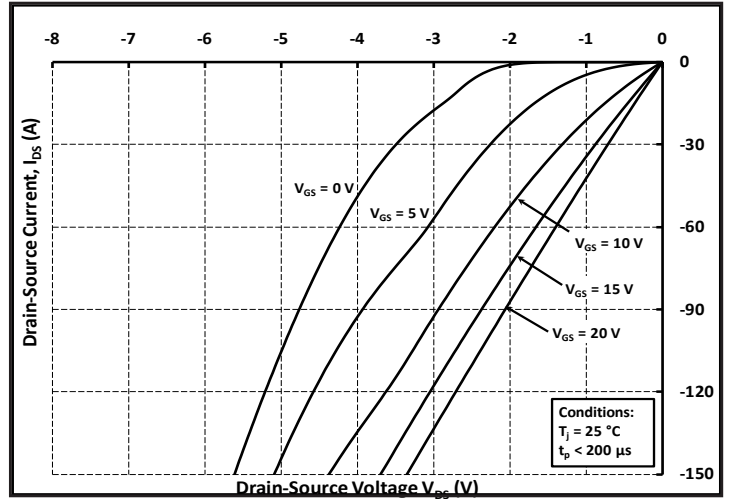


Figure 14. 3rd Quadrant Characteristic at 25 °C

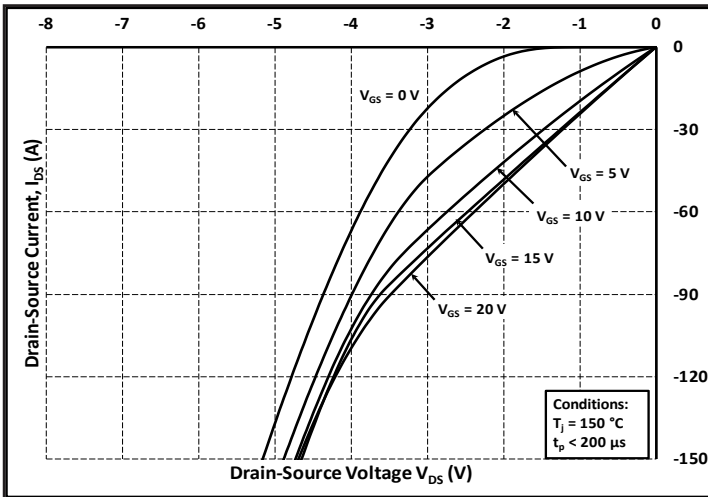


Figure 15. 3rd Quadrant Characteristic at 150 °C

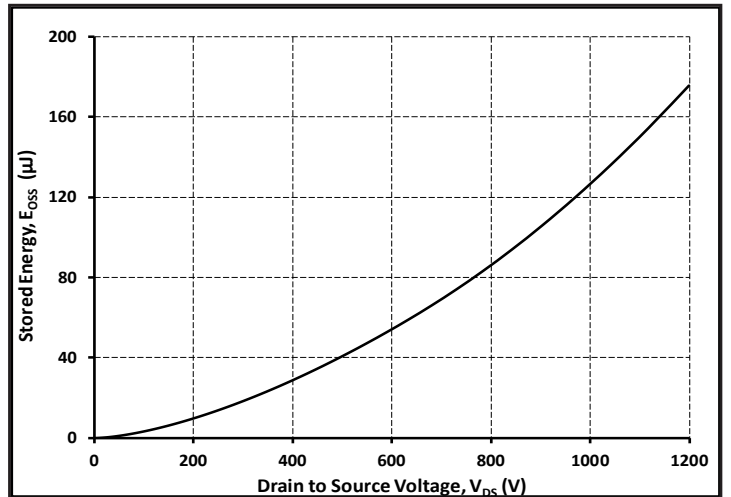


Figure 16. Output Capacitor Stored Energy

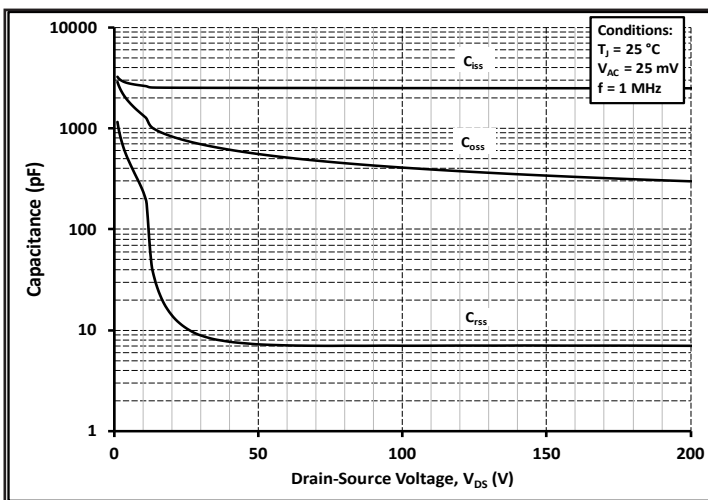


Figure 17. Capacitances vs. Drain-Source Voltage (0-200 V)

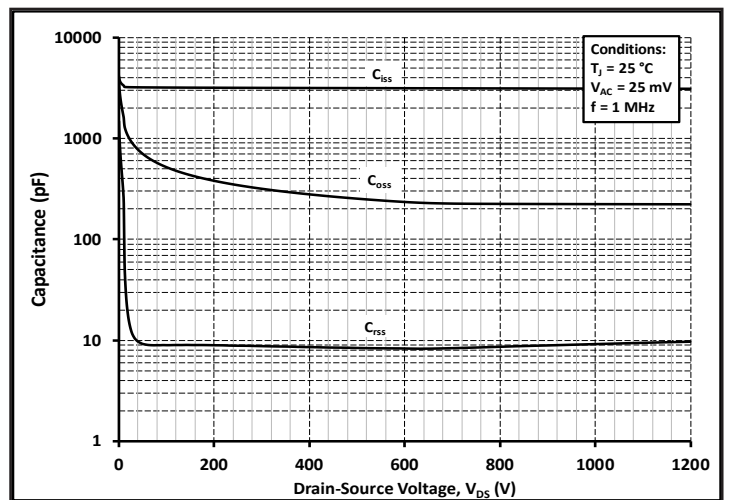


Figure 18. Capacitances vs. Drain-Source Voltage (0-1000 V)

Typical Performance

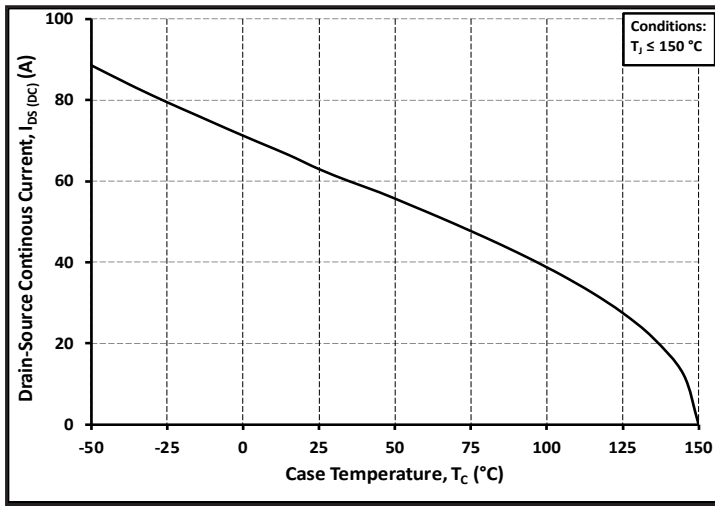


Figure 19. Continuous Drain Current Derating vs. Case Temperature

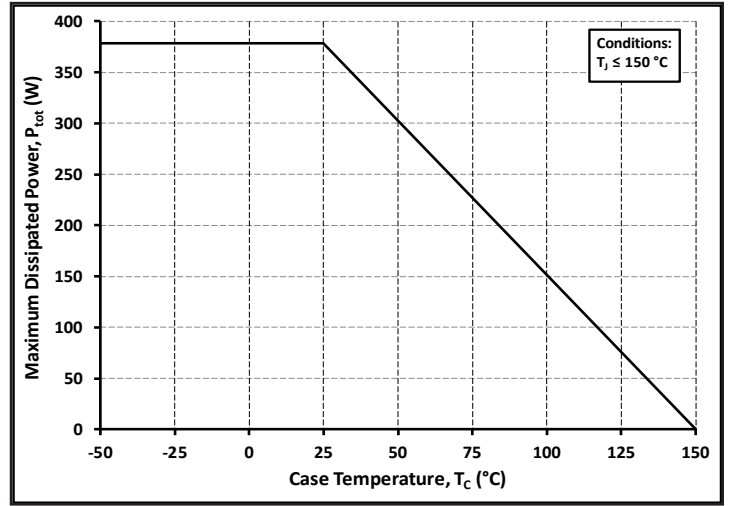


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

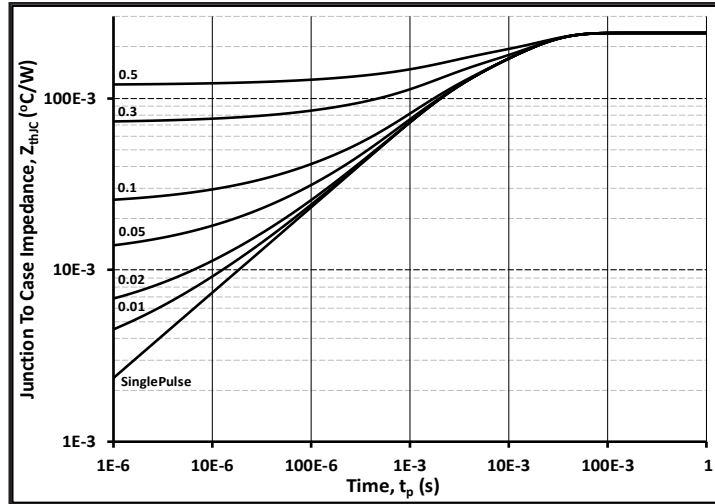


Figure 21. Transient Thermal Impedance (Junction - Case)

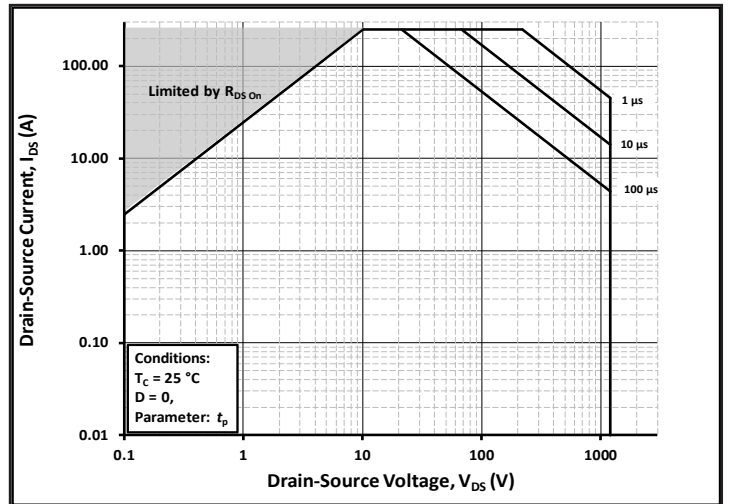


Figure 22. Safe Operating Area

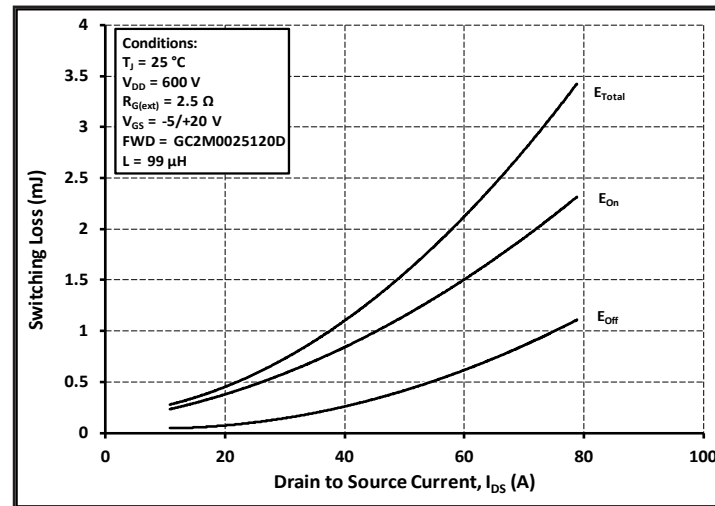


Figure 23. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 600V$)

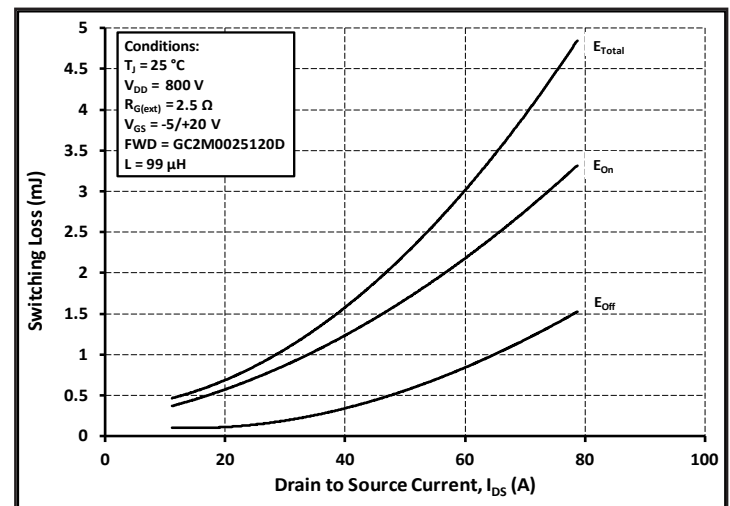


Figure 24. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 800V$)

Typical Performance

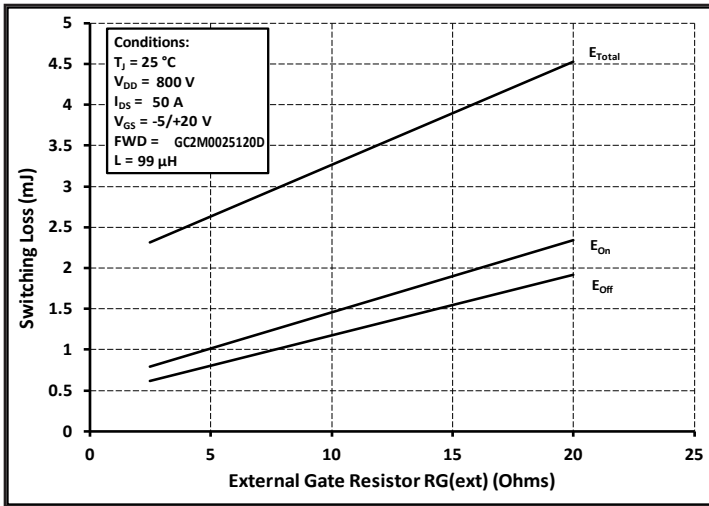


Figure 25. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

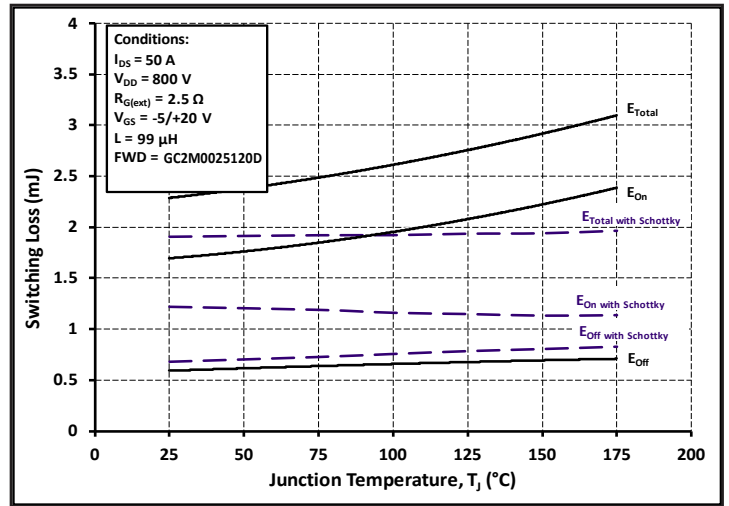


Figure 26. Clamped Inductive Switching Energy vs. Temperature

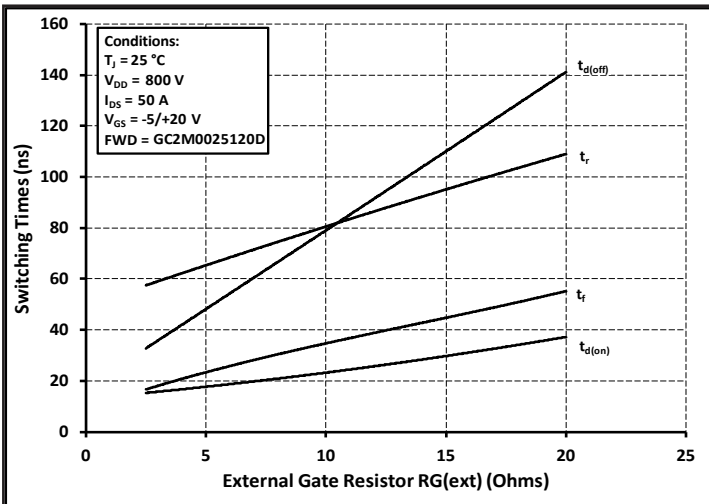


Figure 27. Switching Times vs. $R_{G(ext)}$

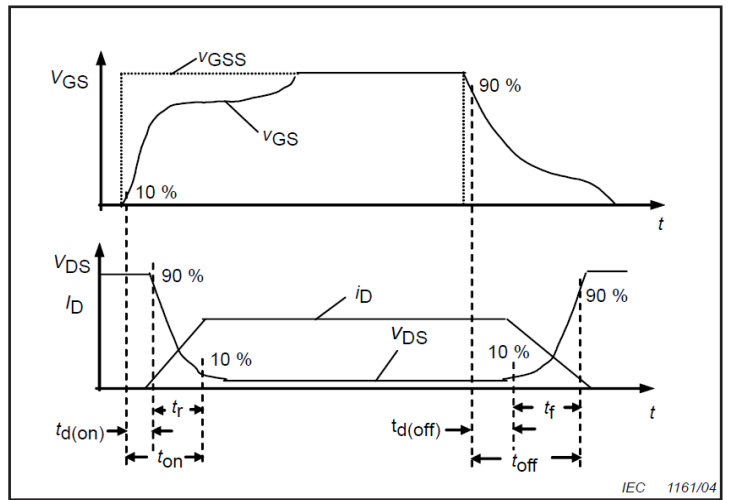


Figure 28. Switching Times Definition

Test Circuit Schematic

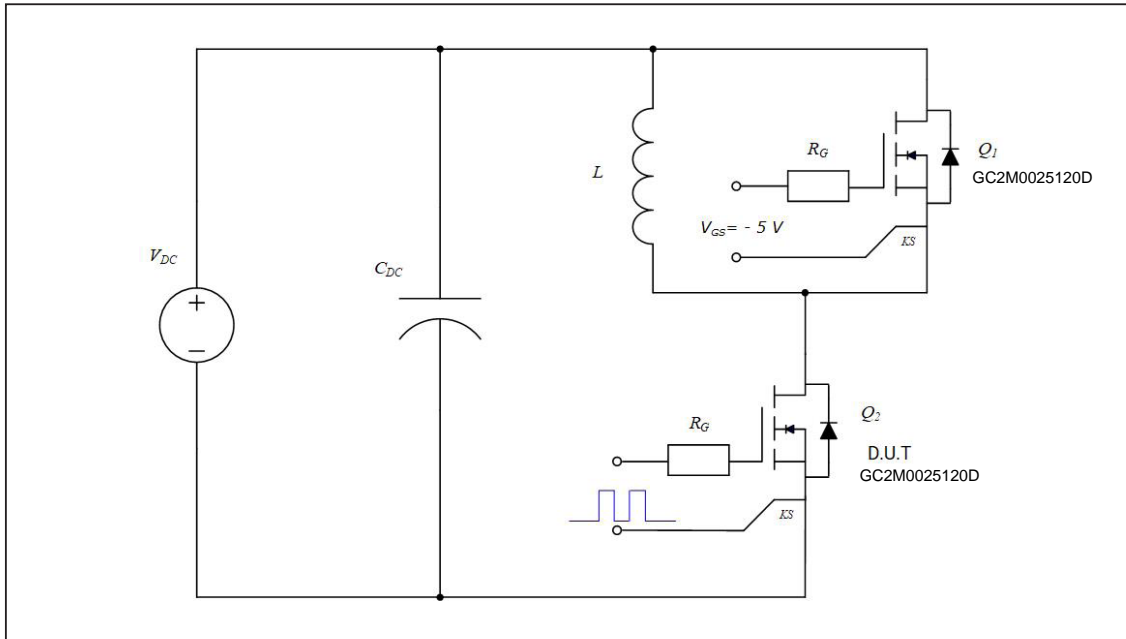


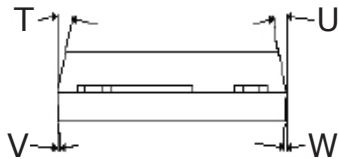
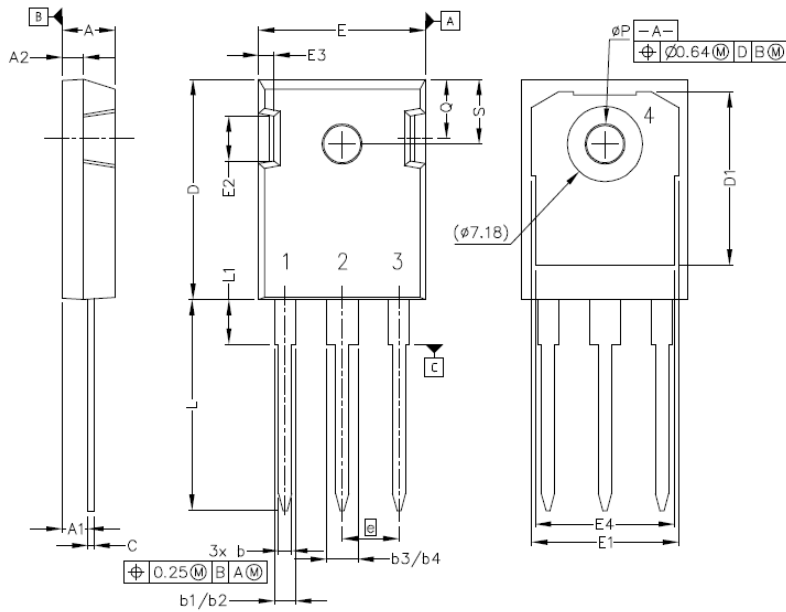
Figure 29. Clamped Inductive Switching
Waveform Test Circuit

ESD Ratings

ESD Test	Resulting Classification
ESD-HBM	3A (4000V - 8000V)
ESD-CDM	C3 ($\geq 1000V$)

Package Dimensions

Package TO-247-3

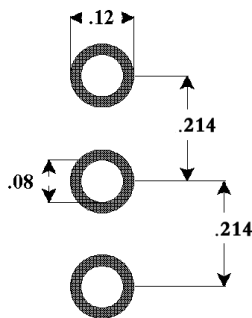


Pinout Information:

- Pin 1 = Gate
- Pin 2, 4 = Drain
- Pin 3 = Source

POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.042	.052	1.07	1.33
b1	.075	.095	1.91	2.41
b2	.075	.085	1.91	2.16
b3	.113	.133	2.87	3.38
b4	.113	.123	2.87	3.13
c	.022	.027	0.55	0.68
D	.819	.831	20.80	21.10
D1	.640	.695	16.25	17.65
D2	.037	.049	0.95	1.25
E	.620	.635	15.75	16.13
E1	.516	.557	13.10	14.15
E2	.145	.201	3.68	5.10
E3	.039	.075	1.00	1.90
E4	.487	.529	12.38	13.43
e	.214 BSC		5.44 BSC	
N	3		3	
L	.780	.800	19.81	20.32
L1	.161	.173	4.10	4.40
ØP	.138	.144	3.51	3.65
Q	.216	.236	5.49	6.00
S	.238	.248	6.04	6.30
T	9°	11°	9°	11°
U	9°	11°	9°	11°
V	2°	8°	2°	8°
W	2°	8°	2°	8°

Recommended Solder Pad Layout



TO-247-3